## EE40 Fall 1999 <br> Mid Term 1 <br> Profeessor

## Problem \#1

Fill in the logic values in the table below for input values given. Note that the value for " C " is given as an example.

c)

write the Intermediate Values and Outputs for $\mathrm{A}=1, \mathrm{~B}=0$ :

|  | C | D | E | F | G | H | I |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| Value |  |  |  |  |  |  |  |

e. All logic blocks in the above figures havea unit gate delay of 10 n sec .


Show the logic values versus time(for $\mathrm{t}=0$ to 70 n sec ) for outputs C and D of example a, given logic input values ( A and B ) shown below.

## Problem \#2

"circuit solution by inspection"

Each of these problems should take no more than 1-2 minutes. WRITE ANSWER IN PLACE PROVIDED. there is no partial credit on these problems
a.
a)


$\mathrm{Vab}=$ $\qquad$
b.
b)


Find $V_{C D}$

Vcd $=$ $\qquad$ _v
c.


## Find power dissipated in 500 K resistor

$\mathrm{P}=$ $\qquad$ w
d.
d)


Find $V_{X}$ and $V_{Y}$

$$
\begin{aligned}
& V x=\_\quad v \\
& V y=\_\_v
\end{aligned}
$$

e.


Find $\mathbf{R}_{\mathrm{AB}}$
Rab $=$ $\qquad$ Kohms
f..


Find $I_{1}$

I1 $=$ $\qquad$ microAmps
g.

$\mathrm{Vx}=$ $\qquad$

## Problem \#3

Initial Conditions

In each of the problems below, find the value of the current or voltage just after the switch moves ( $\mathrm{i}=0+$ ). (What is requested is just a numerical value, Not an equation or function of time.
a.

iR= $\qquad$ microAmps
b.

$\mathrm{Vc}=$ $\qquad$ v
c.

$\mathrm{I} 1=$ $\qquad$ milliAmps
d.

$\mathrm{Vx}=$ $\qquad$ v

## Problem \#4

"Nodal Analysis"
a. For the circuit below you are asked to write sufficient equations to find the unknowns. you MUST put the equations into the space Indicated. Do any scratch work on the page opposite. Do not Solve.


Unknowns: $\mathrm{V}_{\mathrm{a}}, \mathrm{V}_{\mathrm{b}}, \mathrm{V}_{\mathrm{c}}$
b. Similar to part a, you are asked to write sufficient equations to find the unknowns. Do not solve. you


## Problem \#5

The following circuit is used to study one phase of the operation of a DRAM cell $\qquad$ the slow decay of a stored "I". First the switch S1 is closed and kept closed to write a "I". Then it opens and the storage capacitor Cb is supposed to maintain the stored inforamtion. In this memory, a valid " I " is any voltage Vb in the range of 1 to 3 V .

a. What is the value of Vb just after the switch S opens, ie. at $\mathrm{t}=0+?(1 \%$ accuracy is sufficient. $)$
b. What is the value of Vb much later, (e.g. 1 hour later)?
c. on the axes provided on the facing page, neatly sketch the graph of $\mathrm{Vb}(\mathrm{t})$ versus time. You must label the axes with units
d. Write an equation for Vb as a function of time.

## Problem \#6

a. Find the Thevenin Equivalent Circuit of the following


$\mathrm{Vt}=$ $\qquad$ V
$\mathrm{Rt}=$ $\qquad$ Kohms
b. Find the Norton Equivalent of the folowing linear circuit:

$\mathrm{Vn}=$ $\qquad$ V
$\mathrm{Rn}=$ $\qquad$ Kohms
c. Find the powers supplied by the voltage source in the following circuit.
Power out $=$ $\qquad$

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